



Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

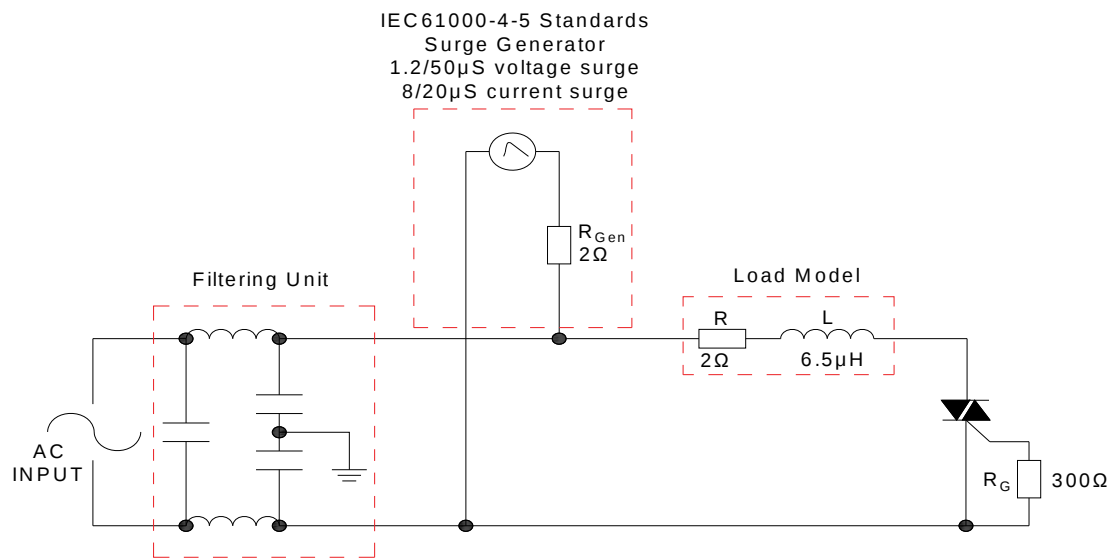
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GT}	$V_D=V_{GS}$ $T_j=25$ $R_L=33k\Omega$	- -	MIN.	0.2	V
I_{GT}	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				60	
I_{IH}	$I_T=50$ mA		MAX.	40	mA

dV/dt $V_D=400V$ Gate Open $T_j 0.2$



ORDERING INFORMATION

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie



PACKAGE MECHANICAL DATA





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